

IN THE CLAIMS:

Kindly amend claims 1-3 and add claims 4-17 as shown in the following listing of claims, which replaces all previous versions and listings of claims in this application.

1. (currently amended) A voltage detecting circuit, comprising:

a first terminal ~~that is connected to~~ with a positive pole of a battery;

a second terminal ~~that is connected to~~ with a negative pole of the battery;

a voltage dividing circuit that divides a voltage across the battery;

a reference voltage circuit that generates a reference voltage;

a comparator that compares outputs a ~~signal on the basis of an output~~ of the reference voltage circuit and ~~an output of the voltage dividing circuit and outputs a comparison signal;~~

a first output circuit ~~that is connected between the first terminal and the second terminal and outputs for outputting a first output signal on the basis of the comparison signal output by signal from the comparator;~~

~~an output terminal that outputs the output signal from the first output circuit; and~~

~~a second output circuit that outputs for outputting a second output signal that changes in value based on a voltage of the battery and to the output terminal on the basis of signals at from the first terminal and the second terminal; and~~

~~an output terminal for outputting the first and second output signals,~~

~~wherein the second output circuit changes over the output signal in accordance with a voltage value of the battery.~~

2. (currently amended) ~~A~~ The voltage detecting circuit according to claim 1; as claimed in claim 1, wherein the second output circuit comprises a depression-type depletion-type n-ch MOS transistor and a depression-type depletion-type p-ch MOS transistor which are connected in series between the output terminal and one of the first terminal and the second terminal; and, wherein a signal based on a voltage of the first terminal is input inputted to a gate electrode of the depression-type depletion-type p-ch MOS transistor, and wherein a signal based on a voltage of the second terminal is input inputted to a gate electrode of the depression-type depletion-type n-ch MOS transistor.

3. (currently amended) ~~A~~ The voltage detecting circuit according to claim 2; as claimed in claim 2, wherein the first output circuit comprises an enhancement-type n-ch MOS transistor and an enhancement-type p-ch MOS transistor which are connected in series between the first terminal and the second terminal; and, wherein a signal based on the comparison signal output by of the comparator is input inputted to gate electrodes of the enhancement-type p-ch MOS transistor and the enhancement-type n-ch MOS transistor, and wherein an absolute values value of any threshold voltages voltage of the depletion-type depression-type n-ch MOS transistor and the depletion-type depression-type p-ch MOS transistor are is larger than an absolute values value of any threshold voltages voltage of the enhancement-type n-ch MOS transistor and the enhancement-type p-ch MOS transistor.

4. (new) A voltage detecting circuit according to claim 2; wherein the first terminal is connected to a gate electrode of the depletion-type p-ch MOS transistor and the second terminal is connected to a gate electrode of the depletion-type n-ch MOS transistor.

5. (new) A voltage detecting circuit according to claim 3; wherein the comparison signal is input to gate electrodes of the enhancement-type p-ch MOS transistor and the enhancement-type n-ch MOS transistor.

6. (new) A voltage detecting circuit according to claim 1; wherein the first output circuit comprises two enhancement mode MOS transistors connected in series between the input terminals.

7. (new) A voltage detecting circuit according to claim 6; wherein the second output circuit comprises two depletion mode MOS transistors connected in series between the output terminal and one of the input terminals.

8. (new) A voltage detecting circuit, comprising: input terminals; an output terminal; a reference voltage generator for generating a reference voltage; a comparator for comparing a voltage across the input terminals with the reference voltage and outputting a comparison signal; a first output circuit connected between the input terminals for outputting a first signal to the output terminal on the basis of the comparison signal; and a second output circuit for outputting a second signal to the output terminal which changes in level based on the signal on the input terminals.

9. (new) A voltage detecting circuit according to claim 8; wherein the input terminals comprise a pair of terminals connected to opposite poles of a battery.

10. (new) A voltage detecting circuit according to claim 6; further comprising a voltage dividing circuit for dividing a voltage across the input terminals and outputting a divided voltage to the comparator.

11. (new) A voltage detecting circuit according to claim 6; wherein the first output circuit comprises two enhancement mode MOS transistors connected in series between the input terminals.

12. (new) A voltage detecting circuit according to claim 6; wherein the two enhancement mode MOS transistors have opposite polarities.

13. (new) A voltage detecting circuit according to claim 12; wherein an output of the comparator is connected to gate electrodes of the enhancement mode MOS transistors.

14. (new) A voltage detecting circuit according to claim 13; wherein the second output circuit comprises two depletion mode MOS transistors connected in series between the output terminal and one of the input terminals.

15. (new) A voltage detecting circuit according to claim 14; wherein the two depletion mode MOS transistors have opposite polarities.

16. (new) A voltage detecting circuit according to claim 15; wherein a gate electrode of one of the depletion mode MOS transistors is connected to one of the input terminals, and a gate electrode of the other depletion mode MOS transistor is connected to another one of the input terminals.

17. (new) A voltage detecting circuit according to claim 16; wherein absolute values of threshold voltage of the depletion mode MOS transistors are larger than absolute values of threshold voltages of the enhancement mode MOS transistors.